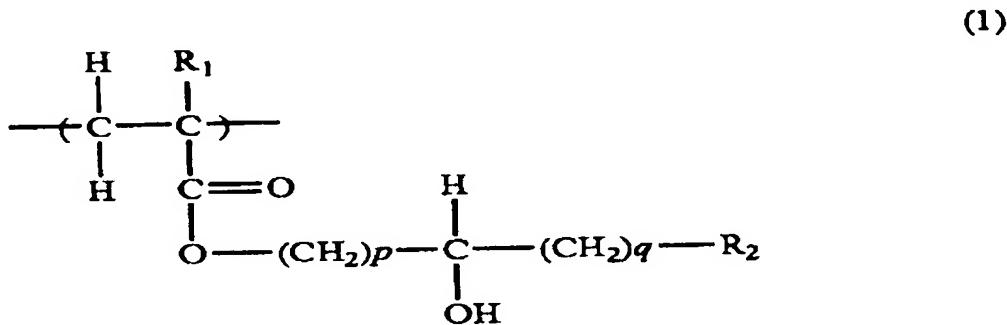


**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

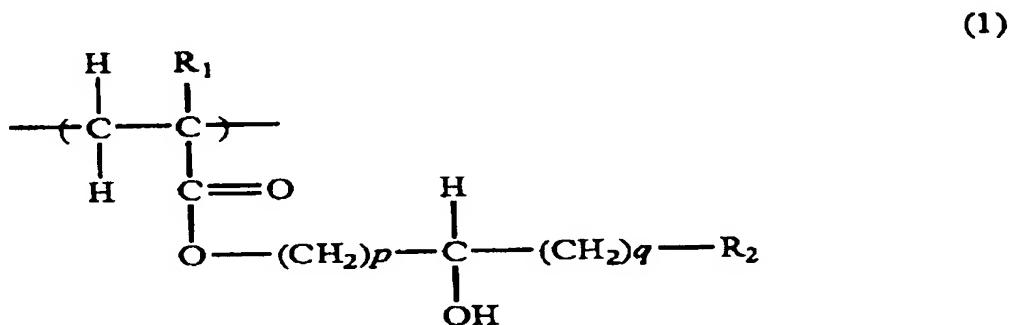
1. (Currently Amended) A gap fill material forming composition wherein the composition is used in manufacture of semiconductor device by a method comprising coating a photoresist on a semiconductor substrate having a hole with aspect ratio shown in height/diameter of 1 or more, and transferring an image to the semiconductor substrate by use of lithography process, and wherein the composition comprises a polymer having a weight average molecular weight of 5,000 to 20,000 that is composed of only structural unit of formula (1)



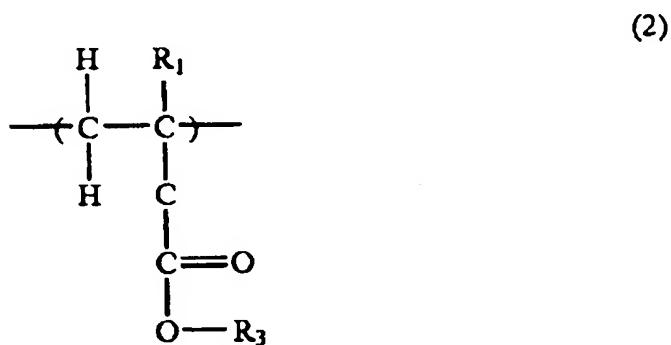
wherein R<sub>1</sub> is hydrogen atom, methyl group, chlorine atom or bromine atom, R<sub>2</sub> is hydrogen atom or hydroxy group, p is the number of 1, 2, 3 or 4, q is the number of 0, 1, 2 or 3, and containing components having a molecular weight of 3000 or less in a rate of 20% or less; a crosslinking agent; and a solvent:solvent selected from the group consisting of butyl lactate, propylene glycol monobutyl ether, propylene glycol monomethyl ether, propylene glycol monomethyl ether acetate and cyclohexanone.

2. (Currently Amended) A gap fill material forming composition wherein the

composition is used in manufacture of semiconductor device by a method comprising coating a photoresist on a semiconductor substrate having a hole with aspect ratio shown in height/diameter of 1 or more, and transferring an image to the semiconductor substrate by use of lithography process, and wherein the composition comprises a polymer having a weight average molecular weight of 5,000 to 20,000 that is composed of structural unit of formula (1) and structural unit of formula (2)



wherein  $R_1$  is hydrogen atom, methyl group, chlorine atom or bromine atom,  $R_2$  is hydrogen atom or hydroxy group,  $p$  is the number of 1, 2, 3 or 4,  $q$  is the number of 0, 1, 2 or 3; and



wherein  $R_1$  is as defined above,  $R_3$  is  $C_{1-8}$  alkyl group, benzyl group,  $C_{1-6}$  alkyl group substituted by at least one fluorine atom, chlorine atom or bromine atom, or  $C_{1-6}$  alkyl group substituted by at least one  $C_{1-6}$  alkoxy group, and the polymer containing components having a molecular weight of 3000 or less in a rate of 20% or less, and containing the structural unit

of formula (1) in a ratio of 0.40 to 0.95; a crosslinking agent; and a solvent, solvent selected from the group consisting of butyl lactate, propylene glycol monobutyl ether, propylene glycol monomethyl ether, propylene glycol monomethyl ether acetate and cyclohexanone,

wherein the sum of the molar ratio of structural unit of formula (1) and the molar ratio of structural unit of formula (2) is 1.

3.-5. (Canceled)

6. (Previously Presented) The gap fill material forming composition according to claim 1, wherein the crosslinking agent is a crosslinking agent having at least two crosslink-forming functional substituents.

7. (Previously Presented) The gap fill material forming composition according to claim 1, further containing an acid or an acid generator.

8. (Previously Presented) A method for forming a gap fill material for use in lithography process of manufacture of semiconductor device, comprising coating the gap fill material forming composition according to claim 1 on a semiconductor substrate having a hole with aspect ratio shown in height/diameter of 1 or more and baking it.

9. (Previously Presented) A method for forming photoresist pattern for use in manufacture of semiconductor device, comprising coating the gap fill material forming composition according to claim 1 on a semiconductor substrate having a hole with aspect ratio shown in height/diameter of 1 or more, baking it to form a gap fill material, forming a photoresist layer on the gap fill material, exposing the semiconductor substrate covered with the gap fill material and the photoresist layer to light, and developing the photoresist layer after the exposure to light.

10. (Original) The method for forming photoresist pattern according to claim 9, further comprising a step of forming an anti-reflective coating before or after the step of forming the gap fill material on the semiconductor substrate.